

MOTOROLA
SEMICONDUCTOR
 TECHNICAL DATA

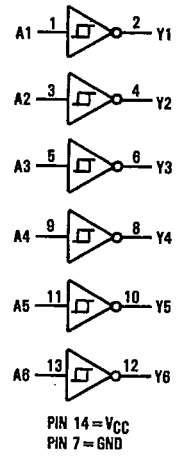
Hex Schmitt-Trigger Inverter
High-Performance Silicon-Gate CMOS

The MC54/74HC14 is identical in pinout to the LS14, LS04, and HC04. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The MC54/74HC14 is useful to "square up" slow input rise and fall times. Due to the hysteresis voltage of the Schmitt trigger, the HC14 finds applications in noisy environments.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 60 FETs or 15 Equivalent Gates

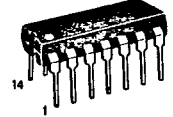
LOGIC DIAGRAM



MC54/74HC14



J SUFFIX
 CERAMIC
 CASE 632-08



N SUFFIX
 PLASTIC
 CASE 646-06



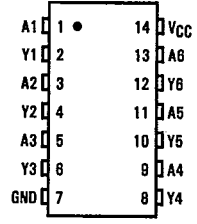
D SUFFIX
 SOIC
 CASE 751A-02

ORDERING INFORMATION

- MC74HCXXN Plastic
- MC54HCXXJ Ceramic
- MC74HCXXD SOIC

$T_A = -55^\circ$ to 125°C for all packages.
 Dimensions in Chapter 7.

PIN ASSIGNMENT



FUNCTION TABLE

Input	Output
A	Y
L	H
H	L

NOT RECOMMENDED FOR NEW DESIGN.



MC54/74HC14

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-1.5 to V _{CC} +1.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
I _{in}	DC Input Current, per Pin	±20	mA
I _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: -10 mW/°C from 65° to 125°C
Ceramic DIP: -10 mW/°C from 100° to 125°C
SOIC Package: -7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 4.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	—	No Limit*	ns

*When V_{in} ≈ 50% V_{CC}, I_{CC} > 1 mA.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				25°C to -55°C	≤85°C	≤125°C	
V _{T+} max	Maximum Positive-Going Input Threshold Voltage (Figure 3)	V _{out} = 0.1 V I _{out} ≤ 20 μA	2.0	1.50	1.60	1.50	V
			4.5	3.15	3.15	3.15	
			6.0	4.20	4.20	4.20	
V _{T+} min	Minimum Positive-Going Input Threshold Voltage (Figure 3)	V _{out} = 0.1 V I _{out} ≤ 20 μA	2.0	1.00	0.95	0.95	V
			4.5	2.30	2.25	2.25	
			6.0	3.00	2.95	2.95	
V _{T-} max	Maximum Negative-Going Input Threshold Voltage (Figure 3)	V _{out} = V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	0.90	0.95	0.95	V
			4.5	2.00	2.05	2.05	
			6.0	2.60	2.65	2.65	
V _{T-} min	Minimum Negative-Going Input Threshold Voltage (Figure 3)	V _{out} = V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	0.30	0.30	0.30	V
			4.5	0.90	0.90	0.90	
			6.0	1.20	1.20	1.20	
V _H max Note 2	Maximum Hysteresis Voltage (Figure 3)	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	1.20	1.20	1.20	V
			4.5	2.25	2.25	2.25	
			6.0	3.00	3.00	3.00	
V _H min Note 2	Minimum Hysteresis Voltage (Figure 3)	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	0.20	0.20	0.20	V
			4.5	0.40	0.40	0.40	
			6.0	0.50	0.50	0.50	

NOTES:

- Information on typical parametric values can be found in Chapter 4.
- V_H min > (V_{T+} min) - (V_{T-} max); V_H max = (V_{T+} max) - (V_{T-} min).

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DC ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				25°C to -55°C	≤85°C	≤125°C	
V _{OH}	Minimum High-Level Output Voltage	V _{in} ≤ V _{T- min} I _{out} ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		V _{in} ≤ V _{T- min} I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	4.5	3.98	3.84	3.70	
			6.0	5.48	5.34	5.20	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} ≥ V _{T+ max} I _{out} ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V _{in} ≥ V _{T+ max} I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	4.5	0.26	0.33	0.40	
			6.0	0.26	0.33	0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	2	20	40	μA

NOTES:

- Information on typical parametric values can be found in Chapter 4.
- V_{Hmin} > (V_{T+ min}) - (V_{T- max}); V_{Hmax} = (V_{T+ max}) - (V_{T- min}).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			25°C to -55°C	≤85°C	≤125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 2)	2.0	125	155	190	ns
		4.5	25	31	38	
		6.0	21	26	32	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0	75	95	110	ns
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	—	10	10	10	pF

NOTES:

- For propagation delays with loads other than 50 pF, see Chapter 4.
- Information on typical parametric values can be found in Chapter 4.

CPD	Power Dissipation Capacitance (Per Inverter) Used to determine the no-load dynamic power consumption: P _D = CPD V _{CC} ² f + I _{CC} V _{CC} For load considerations, see Chapter 4.	Typical @ 25°C, V _{CC} = 5.0 V	pF
		22	

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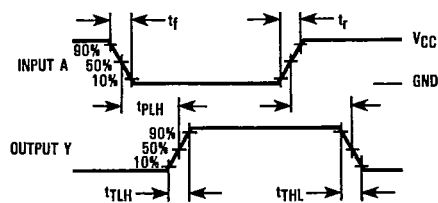
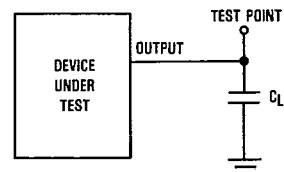


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance.

Figure 2. Test Circuit

MC54/74HC14

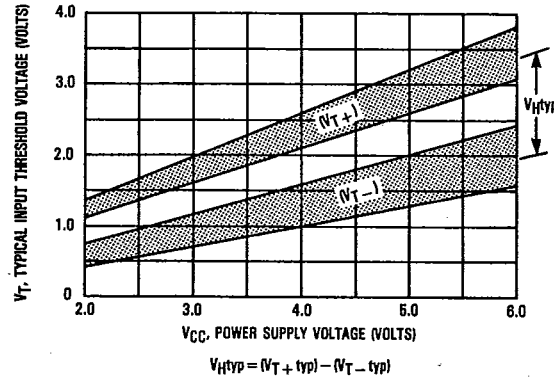


Figure 3. Typical Input Threshold, V_{T+} , V_{T-} Versus Power Supply Voltage

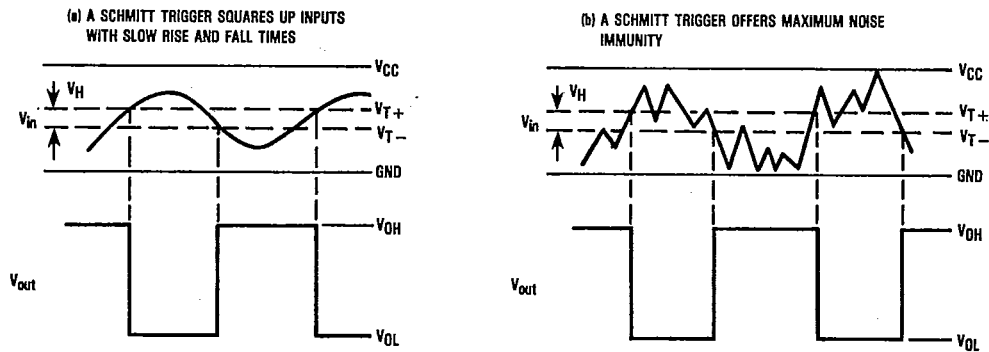


Figure 4. Typical Schmitt-Trigger Applications

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